

SI4866BDY-T1-GE3

SI4866BDY-T1-GE3 Information

	with the sener com	 SI4866BDY-T1-GE3 Vishay Siliconix Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 12V 21.5A 8-SOIC 8-SOIC (0.154", 3.90mm Width) For the pricing/inventory/lead time, please contact	
	For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



SI4866BDY-T1-GE3 Specifications

Manufacturer Part Number	SI4866BDY-T1-GE3
Manufacturer	Vishay Siliconix
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	8-SOIC (0.154", 3.90mm Width)
Series	TrenchFET?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	12V
Current - Continuous Drain (Id) @ 25°C	21.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs(th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	80nC @ 4.5V
Input Capacitance (Ciss) (Max) @ Vds	5020pF @ 6V
Vgs (Max)	$\pm 8 \mathrm{V}$
FET Feature	-
Power Dissipation (Max)	2.5W (Ta), 4.45W (Tc)
Rds On (Max) @ Id, Vgs	5.3 mOhm @ 12A, 4.5V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	8-SO
Package / Case	8-SOIC (0.154", 3.90mm Width)
	Report errors?

SI4866BDY-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4866BDY-T1-GE3 Payment Methods





If you have any question about SI4866BDY-T1-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com